

REMARKS

By this Preliminary Amendment, the specification has been revised to identify the parent application, and claims 1-20 have been canceled. Claim 22-23 have added. Entry of this Preliminary Amendment is respectfully requested.

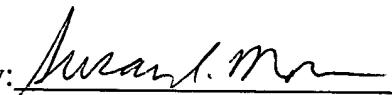
In the event that there are any outstanding matters remaining in the present application, the Examiner is invited to contact Susan S. Morse (Reg. No. 35,292) at (703) 715-0870 in the Washington, D.C. area, to discuss these matters.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies to charge payment or credit any over payment to Deposit Account No. 50-0238 for any additional fee required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17; particularly, extension of time fees.

Respectfully submitted,

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By:


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21. (Amended) A method for fabricating a semiconductor apparatus, comprising [the steps of]:

fabricating a semiconductor substrate which comprises a semiconductor integrated circuit, and an electrode, which is composed of a base member of insulating material formed on the semiconductor integrated circuit and a conductive layer formed on the surface of the base member;

placing the semiconductor substrate to face a connection substrate [according to a face-down technique];

connecting the electrode to the connection substrate; and

[filling] supplying a seal member in the space between the semiconductor substrate and the connection substrate[, wherein

the base member and the seal member are made of the same material].

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